

# 1st Announcement and Call for Papers

## The 29th International Symposium on Power Semiconductor Devices and ICs

# ISPSD 2017

May 28 - June 1, 2017

SAPPORO, Japan

Conference site: Royton Sapporo



ISPSD is the premier forum for technical discussion in all areas of power semiconductor devices and integrated circuits, their hybrid technologies and applications. ISPSD 2017 will be held in the beautiful city Sapporo, the center of Hokkaido island in Japan.

### Main categories of interest include:

- ◆ **High Voltage Power Devices:** Medium and high voltage Si bipolar devices such as IGBT, thyristor, pn diode, etc
- ◆ **Low Voltage Power Devices:** Low and medium voltage Si unipolar devices such as power MOSFETs, SJ type devices, etc
- ◆ **New Material Power Devices:** Power devices based on compound or new materials such as SiC, GaN, diamond
- ◆ **Power ICs:** Integrated power devices and circuitry on a single or multi chip(s) architecture
- ◆ **Module and Package Technologies:** Integrated power modules and packaging technologies (functionality, power density, isolation, reliability, device cooling, temperature endurance, manufacturing, materials, etc)

### < Important date >

Abstract Submission Deadline :  
November 15, 2016

### < Direct Flights to New Chitose Airport >

Seoul (Incheon) , Busan , Shanghai, Taipei , Hong Kong, Bangkok

### < Connecting Flights >

City	Flights / Day	Flight Time
Tokyo, Haneda	54	1:30
Tokyo, Narita	15	1:30
Nagoya (Chubu)	17	1:40
Kansai Int'l	11	1:50
Osaka	10	1:50

### < Airport to Downtown Sapporo >

Airport express train: 37 min. to downtown, available every 10-15 minutes

**General Chair:** Dr. Mutsuhiro Mori, Hitachi, Ltd.

**Vice General Chair:** Dr. Kimimori Hamada, Toyota Motor Corporation

**Technical Program Chair:** Prof. Ichiro Omura, Kyushu Institute of Technology

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